

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It combines one N Channel MOSFET and one P channel MOSFET.

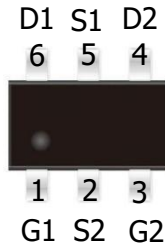
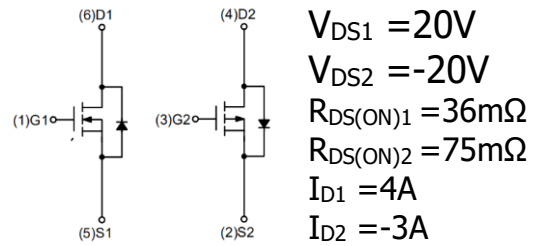
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

Application

- Power Management in Notebook Computer
- BLDC Motor driver

Product Summary



SOT23-6



Ordering Information:

Part NO.	ZMC88212U
Marking	88212
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

N Channel Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$I_{D@T_C=25^\circ C}$	4	A
	$I_{D@T_C=75^\circ C}$	3	A
	$I_{D@T_C=100^\circ C}$	2.5	A
Pulsed Drain Current ①	I_{DM}	12	A
Total Power Dissipation	$P_D@T_C=25^\circ C$	2.1	W
Total Power Dissipation	$P_D@T_A=25^\circ C$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	5	mJ

•P Channel Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$I_{D@T_C=25^\circ\text{C}}$	-3	A
	$I_{D@T_C=75^\circ\text{C}}$	-2.3	A
	$I_{D@T_C=100^\circ\text{C}}$	-1.9	A
Pulsed Drain Current ①	I_{DM}	-9	A
Total Power Dissipation	$P_D@T_C=25^\circ\text{C}$	9	W
Total Power Dissipation	$P_D@T_A=25^\circ\text{C}$	0.45	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	5	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	60	$^\circ\text{C/W}$
Thermal resistance, junction - ambient	R_{thJA}	-	-	100	$^\circ\text{C/W}$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^\circ\text{C}$

•N Channel Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.5	0.8	1.2	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 4A$		36	50	m Ω
		$V_{GS} = 2.5V, I_D = 3A$		50	65	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 1A$		2		s

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
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Input capacitance	Ciss	f = 1MHz	-	293	-	pF
Output capacitance	Coss		-	28	-	
Reverse transfer capacitance	Crss		-	25	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Qg	V _{DD} =15V	-	8	-	nC
Gate - Source charge	Qgs	I _D = 4A	-	0.4	-	
Gate - Drain charge	Qgd	V _{GS} = 10V	-	1.5	-	

•P Channel Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.8	-1.2	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-3A		75	100	mΩ
		V _{GS} =-2.5V, I _D =-2.5A		95	120	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-1A		1.5		s

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	Ciss	f = 1MHz	-	430	-	pF
Output capacitance	Coss		-	74	-	
Reverse transfer capacitance	Crss		-	68	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Qg	V _{DD} = -15V	-	10.7	-	nC
Gate - Source charge	Qgs	I _D = -3A	-	0.6	-	
Gate - Drain charge	Qgd	V _{GS} = -10V	-	2.2	-	

•N Channel characteristics curve

Fig.1 Power Dissipation

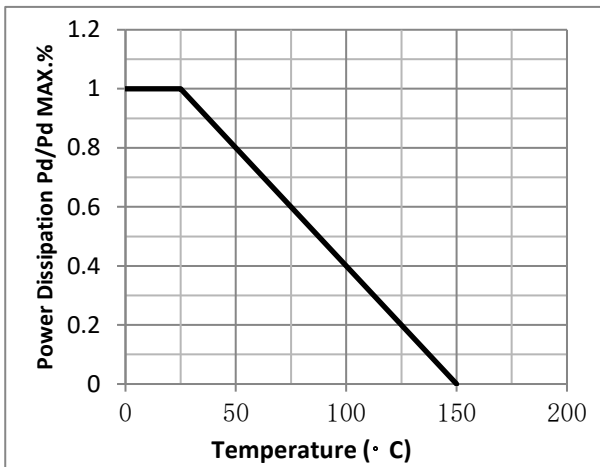


Fig.2 Typical output Characteristics

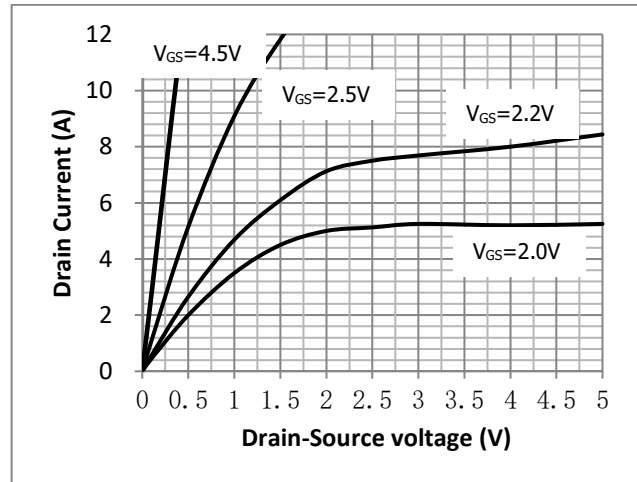


Fig.3 Threshold Voltage V.S Junction Temperature

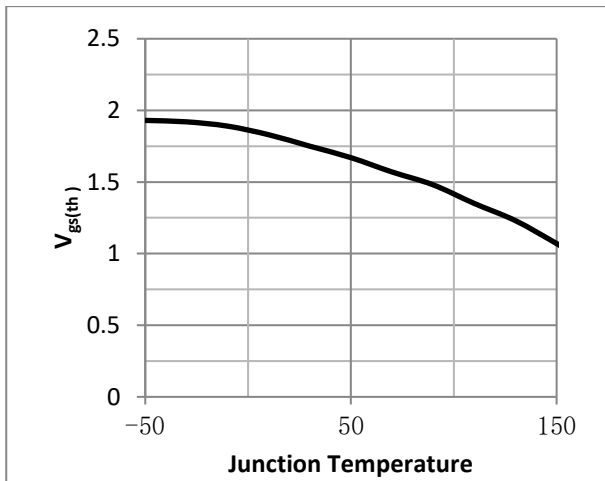


Fig.4 Resistance V.S Drain Current

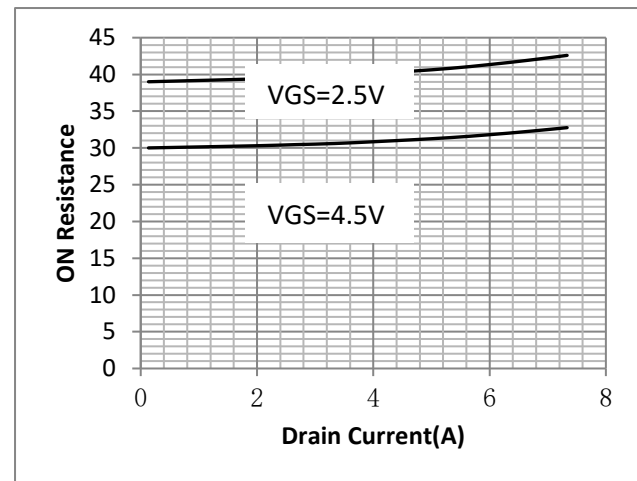


Fig.5 On-Resistance VS Gate Source Voltage

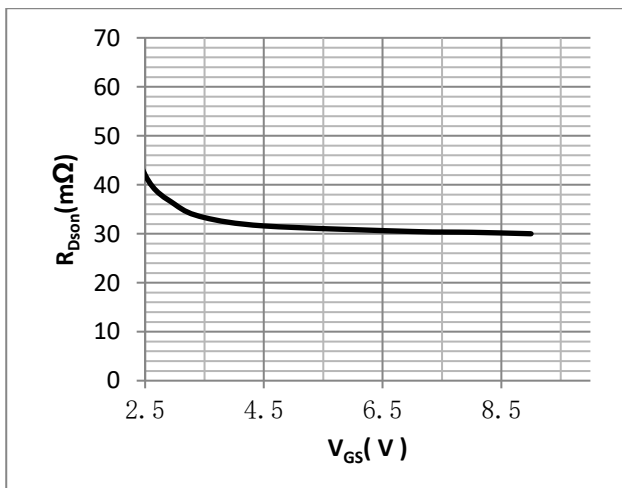


Fig.6 On-Resistance V.S Junction Temperature

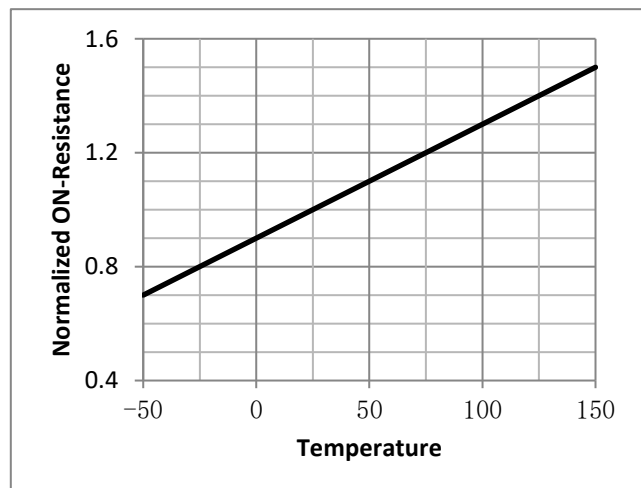


Fig.7 Gate-Charge Characteristics

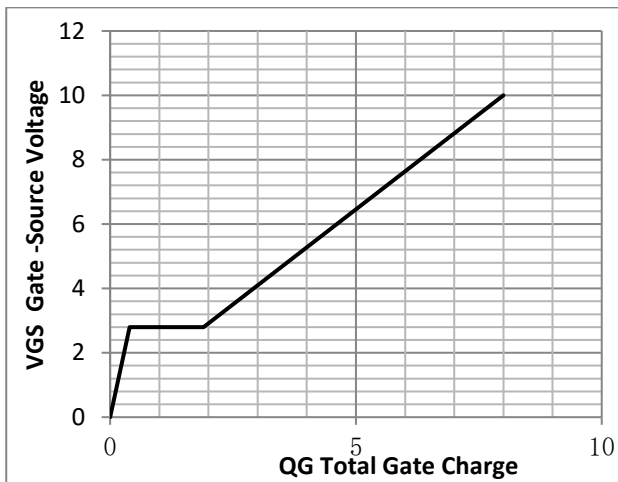


Fig.8 Capacitance Characteristics

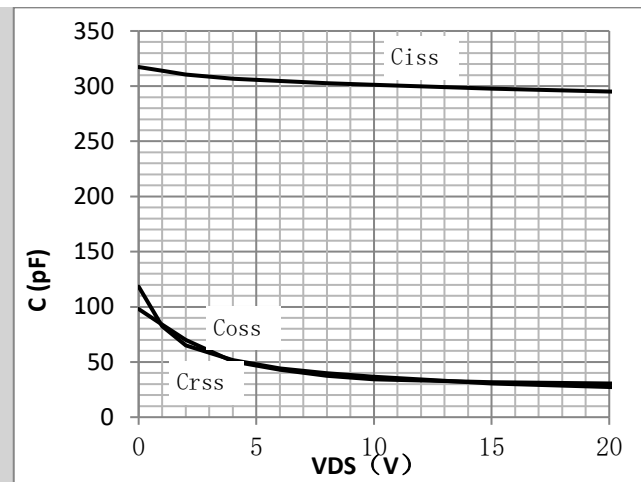


Fig.9 SOA Maximum Safe Operating Area

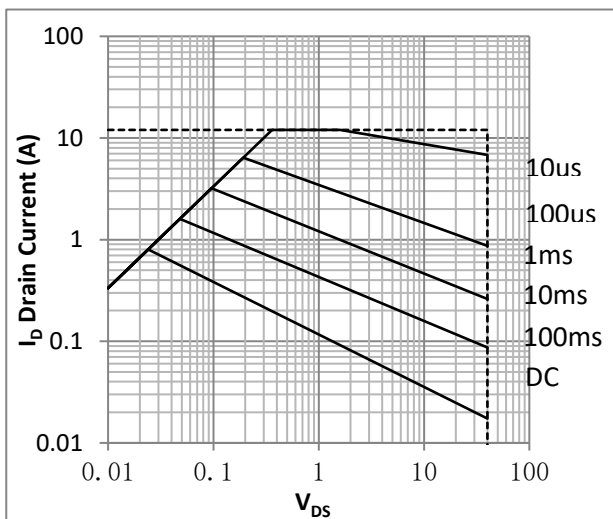
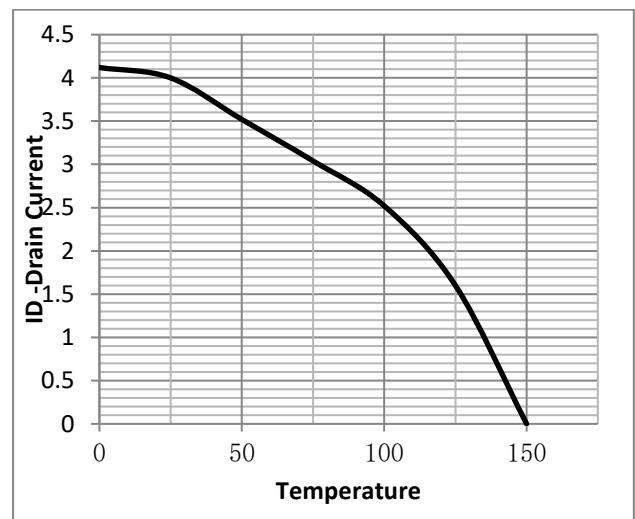


Fig.10 ID-Junction Temperature



•P Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

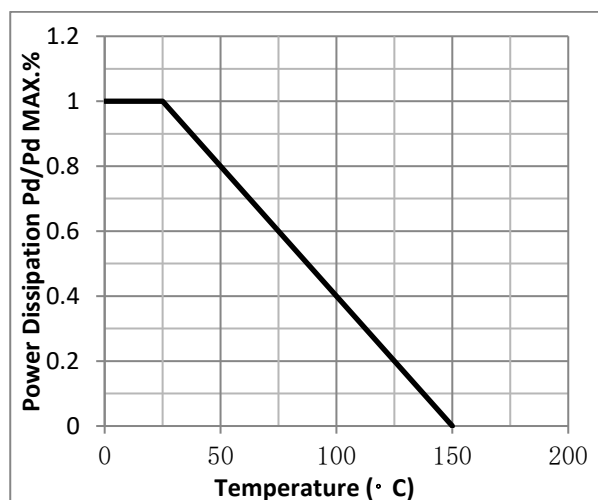


Fig.2 Typical output Characteristics

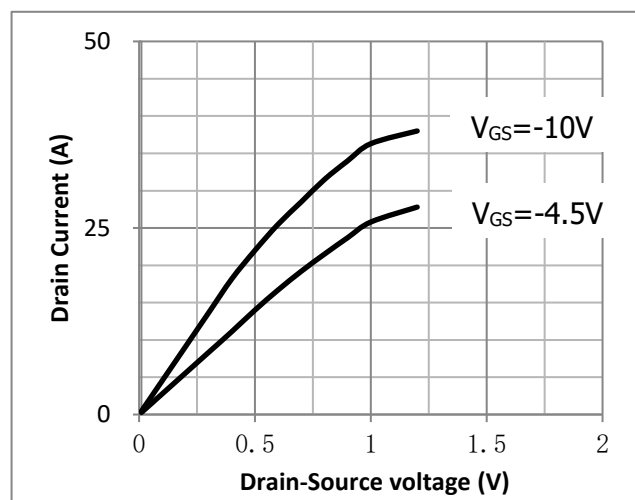


Fig.3 Threshold Voltage V.S Junction Temperature

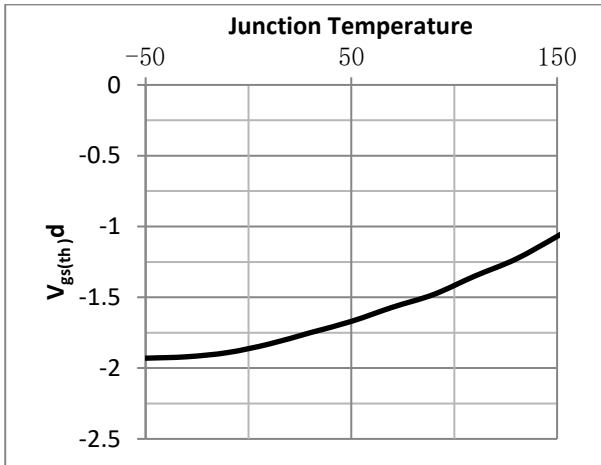


Fig.4 Resistance V.S Drain Current

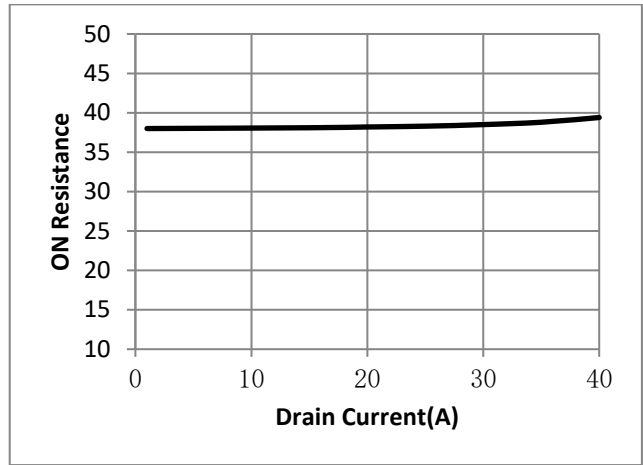


Fig.5 On-Resistance VS Gate Source Voltage

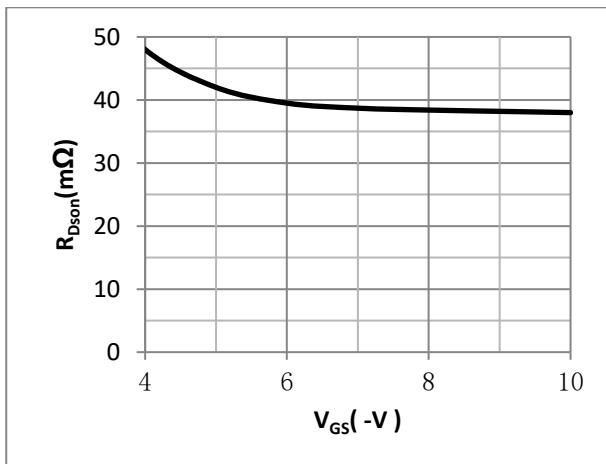


Fig.6 On-Resistance V.S Junction Temperature

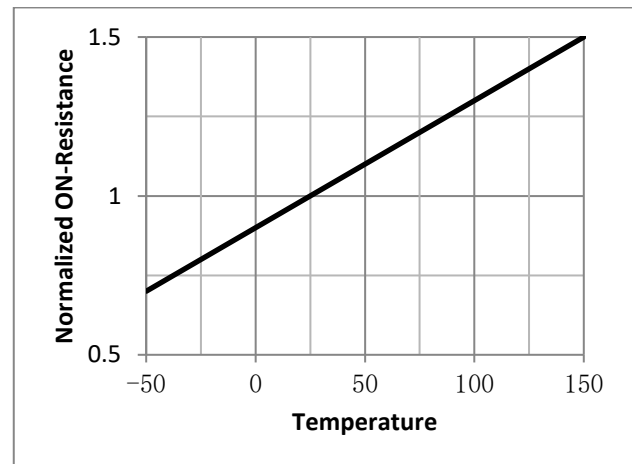


Fig.7 Gate-Charge Characteristics

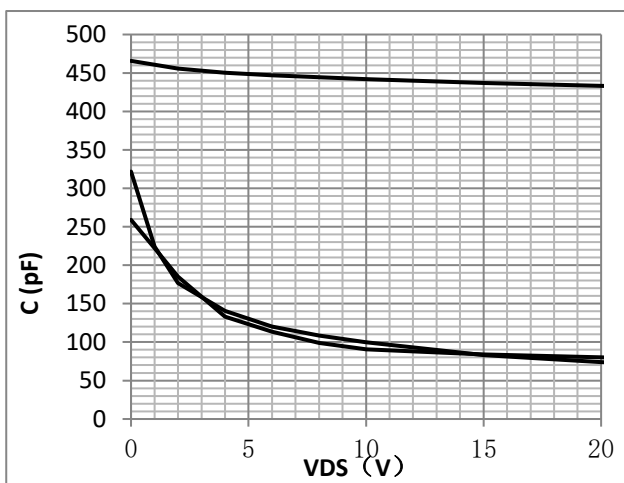


Fig.8 Capacitance Characteristics

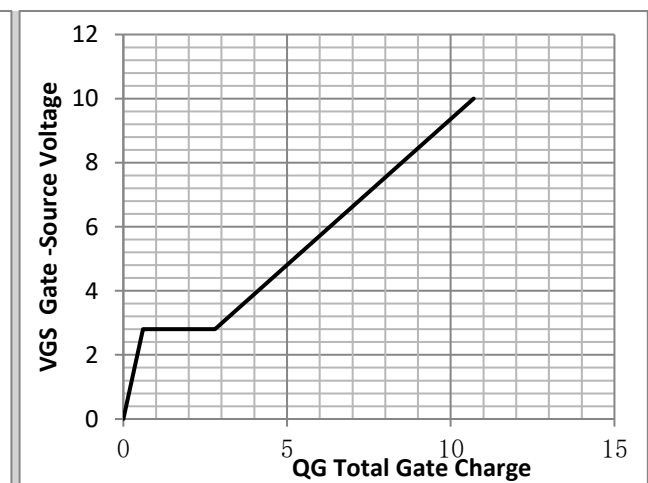


Fig.9 SOA Maximum Safe Operating Area

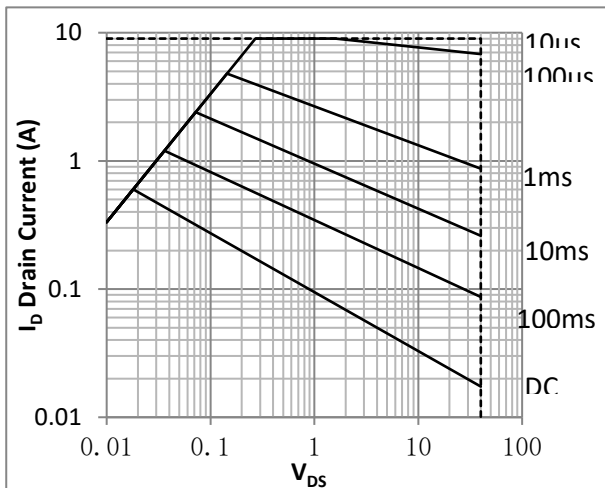
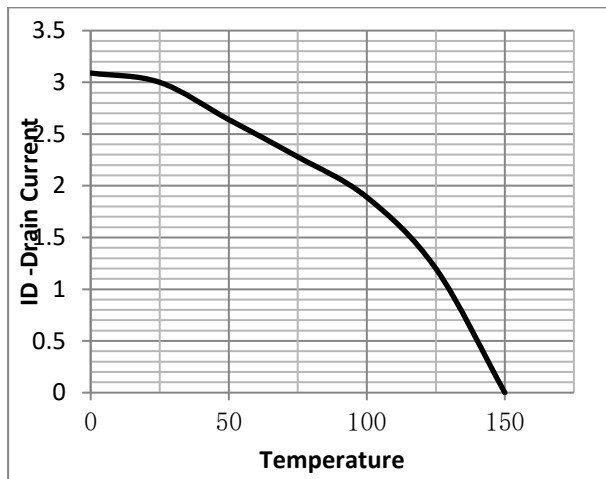


Fig.10 I_D -Junction Temperature



•Test Circuit

Fig.1 Switching Time Measurement Circuit

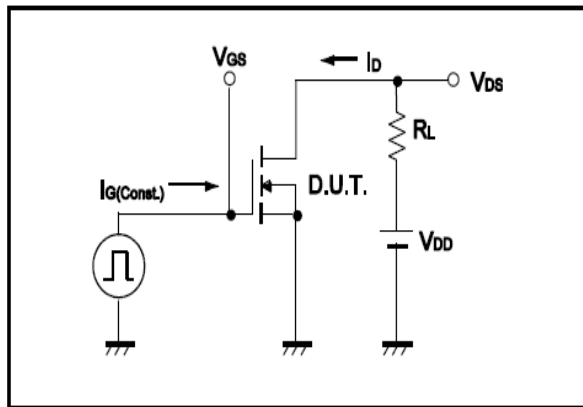


Fig.2 Gate Charge Waveform

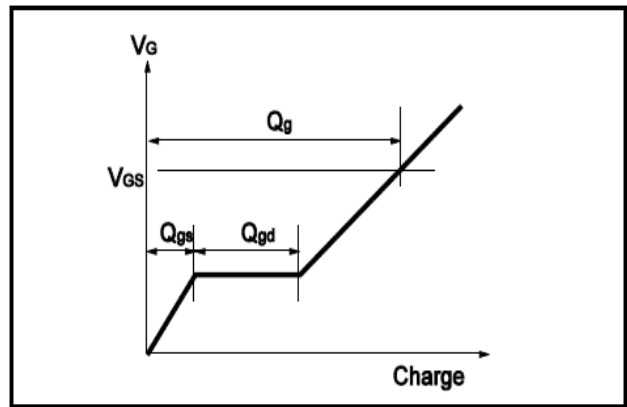


Fig.3 Switching Time Measurement Circuit

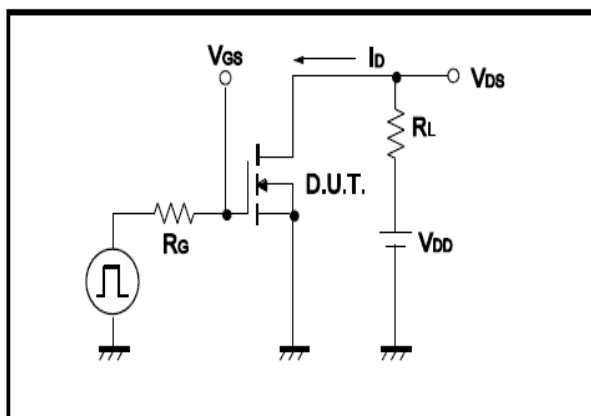


Fig.4 Gate Charge Waveform

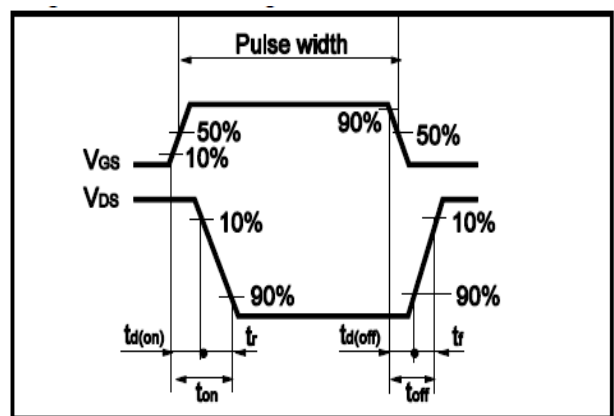


Fig.5 Avalanche Measurement Circuit

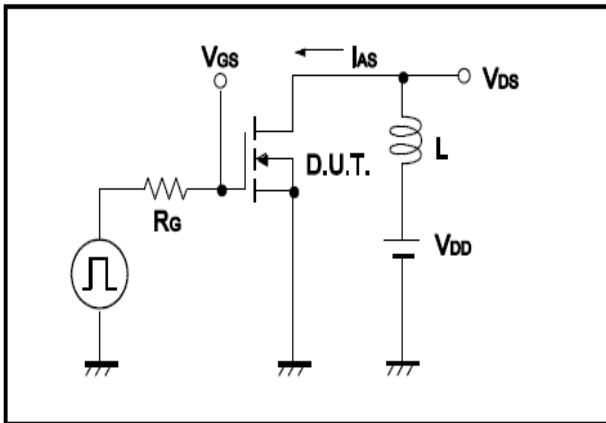
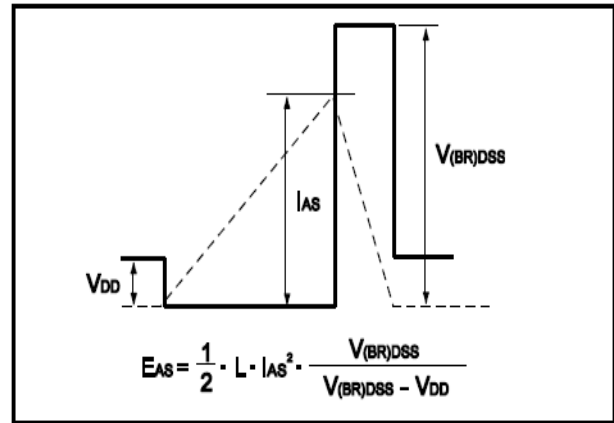


Fig.6 Avalanche Waveform



**•Dimensions(SOT23-6)**

Unit: mm

